

## BDW83C BDW84C

# COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

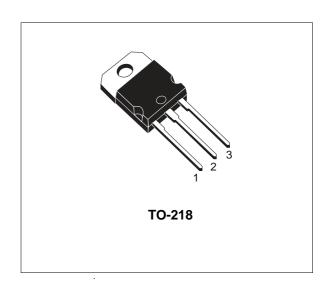
- BDW83C IS A STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP NPN DEVICES
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH DC CURRENT GAIN

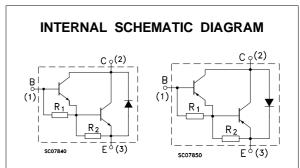
#### **APPLICATIONS**

 LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

#### **DESCRIPTION**

The BDW83C is a Silicon Epitaxial-Base NPN power monolithic Darlington transistor mounted in Jedec TO-218 plastic package. It is intended for use in power linear and switching applications. The complementary type is BDW84C.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit	
		NPN	BDW83C		
		PNP	BDW84C		
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		100	V	
$V_{CEO}$	Collector-Emitter Voltage (I <sub>B</sub> = 0)		100	V	
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		5	V	
Ic	Collector Current		15	Α	
I <sub>CM</sub>	Collector Peak Current		40	Α	
Ι <sub>Β</sub>	Base Current		0.5	A	
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> ≤ 25 °C		130	W	
$T_{stg}$	Storage Temperature		-65 to 150	°C	
Tj	Max. Operating Junction Temperature		150	°C	

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#### BDW83C / BDW84C

#### THERMAL DATA

### **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

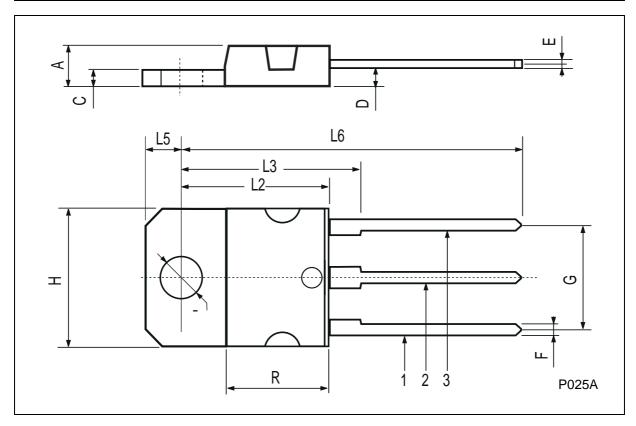
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 100 V V <sub>CB</sub> = 100 V	T <sub>C</sub> = 150 °C			500 5	μA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 40 V				1	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V				2	mA
$V_{\text{CEO(sus)}^{*}}$	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA		100			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6 A I <sub>C</sub> = 15 A	$I_B = 12 \text{ mA}$ $I_B = 150 \text{ mA}$			2.5 4	V
V <sub>BE(on)</sub> *	Base-Emitter Voltage	Ic = 6 A	V <sub>CE</sub> = 3 V			2.5	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 6 A I <sub>C</sub> = 15 A	V <sub>CE</sub> =3 V V <sub>CE</sub> =3 V	750 100		20000	
V <sub>f</sub>	Diode Forward Voltage	I <sub>F</sub> = 10 A				4	V
t <sub>on</sub> t <sub>off</sub>	RESISTIVE LOAD Turn-on Time Turn-off Time	$V_{CC} = 30 \text{ V}$ $R_{B1} = 300 \Omega$ $I_{B1} = -I_{B2} = 40 \text{ mA}$	$I_{C} = 10 \text{ A}$ $R_{B2} = 150 \Omega$		0.9 6		μs μs

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<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP type voltage and current values are negative.

## TO-218 (SOT-93) MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.7		4.9	0.185		0.193
С	1.17		1.37	0.046		0.054
D		2.5			0.098	
Е	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
Н	14.7		15.2	0.578		0.598
L2	_		16.2	_		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	_		12.2	_		0.480
Ø	4		4.1	0.157		0.161



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